Ordering number: EN 2261A

SANYO

No.2261A

2SA1562

PNP Epitaxial Planar Silicon Transistor

High-h_{FE}, AF Amp Applications

Applications

. AF amp, various drivers

Features

. Adoption of MBIT process
. High DC current gain
. Large current capacity
. Low collector to emitter saturation voltage
. High V_{EBO}

Absolute Maximum Ratings at Ta=25°C

				unit
Collector to Base Voltage	V_{CBO}		-30	V
Collector to Emitter Voltage	V_{CEO}		-25	V
Emitter to Base Voltage	V_{EBO}		-15	V
Collector Current	I_C		-1.2	A
Collector Current(Pulse)	I_{CP}		-2	A
Collector Dissipation	P_C		1	W
		Tc=25°C	15	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	V_{CB}=-20V, I_E=0			-1	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=-10V, I_C=0			-1	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=-5V, I_C=-100mA	500	800	1200	
	$h_{FE(2)}$	V_{CE}=-5V, I_C=-10mA	350			
Gain-Bandwidth Product	f_T	V_{CE}=-10V, I_C=-50mA		130		MHz
Output Capacitance	c_{ob}	V_{CB}=-10V, f=1MHz		40		pF
C-E Saturation Voltage	$V_{CE(sat)}$	I_C=-500mA, I_B=-10mA		-0.1	-0.5	V
B-E Saturation Voltage	$V_{BE(sat)}$	I_C=-500mA, I_B=-10mA		-0.78	-1.1	V

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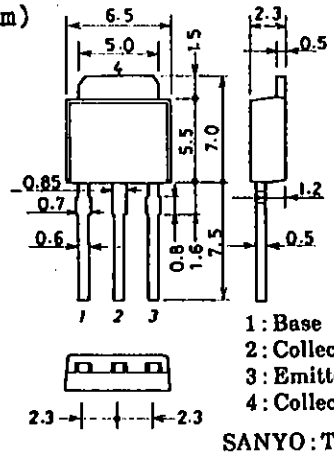
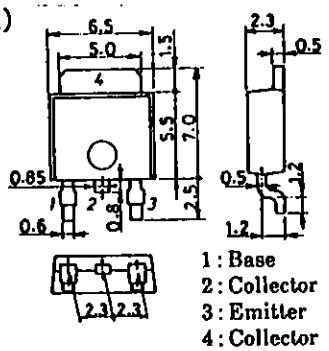
Package Dimensions 2045B
(unit: mm)



1 : Base
2 : Collector
3 : Emitter
4 : Collector

SANYO : TP

Package Dimensions 2044B
(unit: mm)



1 : Base
2 : Collector
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SANYO : TP-FA

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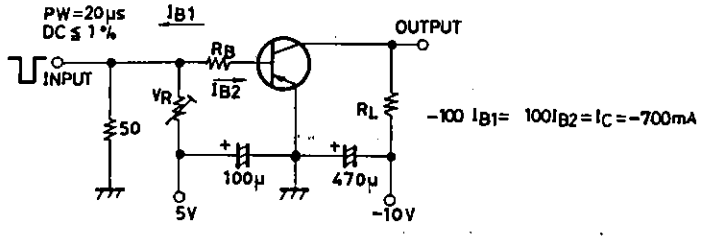
			min	typ	max	unit
C-B Breakdown Voltage	$V_{(BR)CBO}$	I_C=(-)10μA, I_E=0	-30			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	I_C=-1mA, R_{BE}=∞	-25			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	I_E=-10μA, I_C=0	-15			V
Turn-ON Time	t_{on}	See specified Test Circuit.		0.31		μs
Storage Time	t_{stg}	"		0.88		μs
Fall Time	t_f	"		0.23		μs

Switching Time Test Circuit



Unit (Resistance : Ω, Capacitance : F)